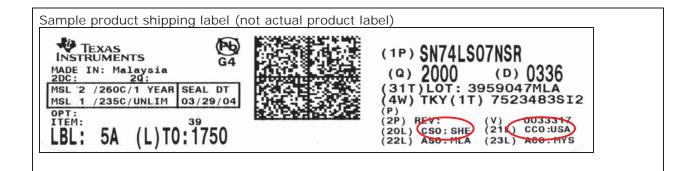
PCN Number:			20130628004 PC							PCN Date: 06/28/2013		
Title:		Transfer of the TPD4E101DPWR device (Vertical Diode-BD process node) to CFAB Facility										
Customer Contact:					N Ma	anager P	Dept: Quality Services					
Proposed 1 st Ship Dat				te:		09/28/201	< -				Date available upon sample request	
Char	nge 1	Гуре:										
Assembly Site					Assembly	v Process				Assembly Materials		
	Desi						ecification	ħ		Mechanical Specification		
Test Site						Shipping/Labeling				Test Process		
Wafer Bump Site				H		ump Material				Wafer Bump Process		
Wafer Fab Site						and Materials				Wafer Fab Process		
											Walter Fab Frocess	
PCN Details												
Description of Change:												
This change notification is to announce the transfer of the TPD4E101DPWR device (Vertical Diode – Bi-Directional process node) from HIJI to the CFAB facility. This will also include a wafer diameter change from 6" to 8".												
Cur	rent						Nev	N				
Site	, pro	cess, wa	afer di	a.			Site	e, process, wafer o	di	a.		
HIJI	/ VD-	BD, 150r	nm				CF	AB/ VD-BD, 200m	m			
Reas	on f	or Char	ıge:									
Continuity of Supply. HIJI site shutdown.												
Antio	cipat	ed imp	act o	n Fo	orm	i, Fit, Fund	ctio	n, Quality or Rel	ia	bil	lity (positive / negative):	
None												
Char	iges	to proc	luct i	den	tifi	cation res	ulti	ng from this PCN	۷:			
Curr	ent											
Chip	Chip Site			Chi	p si	ite code (20	OL)	Chip country coo	de	(2	21L)	
			HIJ				JPN					
				1115				5111				
	New Chip Site Chip site code Chip country code											
Chip Site					ite code		Chip country co	00	je			
	D)L) 2			(21L)				
CFAB				CU	5			CHN				
<u>Fab</u> 1	[den	tificatio		То	psid	de Symbo	l Ma	rking:				
Curr	rent		HIJI					A1				
New CFAE			B				A2					



Product Affected:

TPD4E101DPWR

Qualification Data (Approved 6/11/2013)								
This qualification has been developed for the validation of this change. The qualification data will								
validate that the proposed change meets the applicable released technical specifications.								
Qual Vehicle: TPD4E101DPWR								
Wafer Fab Site: CFAB			Metallization: AICuTiW					
Wafer Fab Process: VD			Wafer Diameter:	200mm				
Qualification:	Plan 🛛 🛛] Te	st Results					
Reliability Test		Со	nditions	Sample Size/Fails Lot#1 Lot#2 Lot#3				
HTOL High Temp Op	Life	15	0C (300 Hrs)	77/0	77/0	77/0		
Electrical Characteriz	ation	-		Pass	-	-		
**High Temp. Storag	ge Bake	17	0C (420 Hrs) ^{note 1}	77/0	77/0	77/0		
**Biased HAST		13	0C/85%RH (96 Hrs)	77/0	77/0	77/0		
**Autoclave 121C		12	1C, 2 atm (96 Hrs)	77/0	77/0	77/0		
**Temperature Cycle	9	-65	5C/+150C (500 Cycle	77/0	77/0	77/0		
ESD CDM		50	OV V	3/0	3/0	3/0		
ESD HBM		20	00V	3/0	3/0	3/0		
Latch-up note 2		-		N/A	N/A	N/A		
**Preconditioning: Level 1-260C								

**Preconditioning: Level 1-260C

Note 1: 420hrs @ 170C is equivalent to 1000hrs @ 150C storage life bake, based on activation energy of 0.7eV.

Note 2: Latch-up is a power up test to check for current paths from I/O pins to power. The TPD4E101DPWR is a diode device with no power pin-with no concern of an SCR, therefore latch-up testing is not a required test for this qualification.

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com